



# STD10NF06L

## N-CHANNEL 60V - 0.1Ω - 10A DPAK STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD10NF06L	60V	<0.12Ω	10A

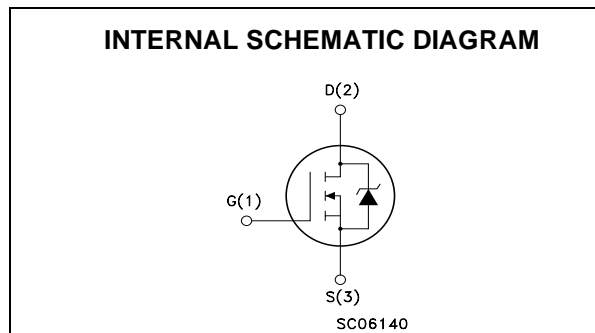
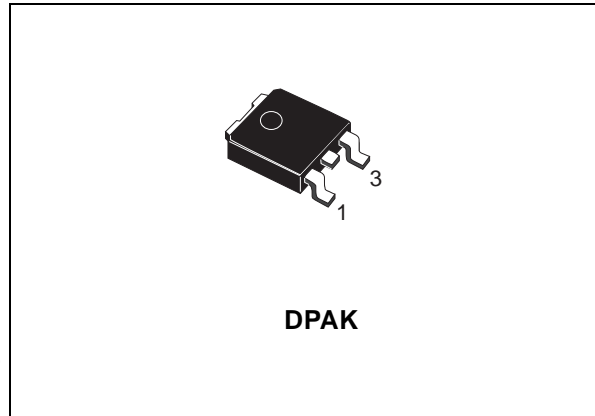
- TYPICAL R<sub>DS(on)</sub> = 0.1Ω
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")

### DESCRIPTION

This MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

### APPLICATIONS

- DC-DC & DC-AC CONVERTERS
- DC MOTOR CONTROL



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	60	V
V <sub>GS</sub>	Gate- source Voltage	± 15	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	10	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	7	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	40	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	30	W
	Derating Factor	0.2	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	30	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	50	mJ
T <sub>stg</sub>	Storage Temperature	- 55 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature		

(●) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 10A, di/dt ≤ 400A/μs, V<sub>DD</sub> = 48V, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(2) Starting T<sub>j</sub> = 25°C, I<sub>d</sub> = 7A, V<sub>DD</sub> = 20 V

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### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	100	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose	275	°C

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 15V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1			V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5 A V <sub>GS</sub> = 5 V, I <sub>D</sub> = 5 A		0.1 0.12	0.12 0.14	Ω Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10A		6		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		346		pF
C <sub>oss</sub>	Output Capacitance			54		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			22		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30V, I_D = 5A$ $R_G = 4.7\Omega, V_{GS} = 4.5V$ (see test circuit, Figure 3)		10		ns
$t_r$	Rise Time			50		ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 48V, I_D = 10A,$ $V_{GS} = 5V$		6 3 2.5	8	nC nC nC

**SWITCHING OFF**

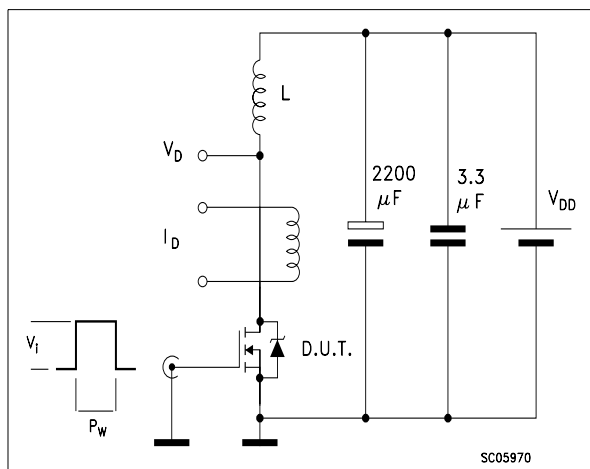
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 30V, I_D = 5A,$ $R_G = 4.7\Omega, V_{GS} = 4.5V$ (see test circuit, Figure 5)		20		ns
$t_f$	Fall Time			10		ns

**SOURCE DRAIN DIODE**

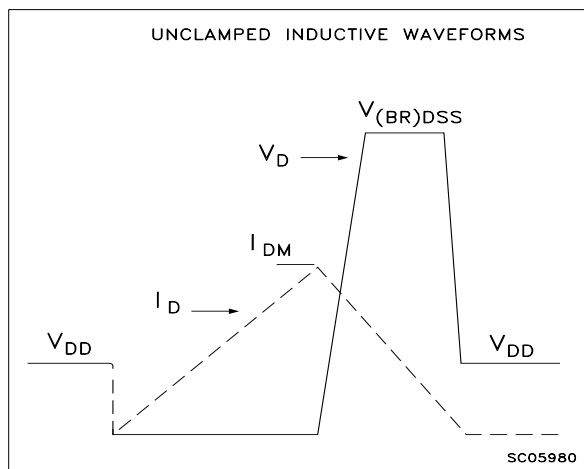
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				10	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				40	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 10A, V_{GS} = 0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 10A, di/dt = 100A/\mu s,$ $V_{DD} = 20V, T_j = 150^\circ C$ (see test circuit, Figure 5)		30 50 3		ns nC A

Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

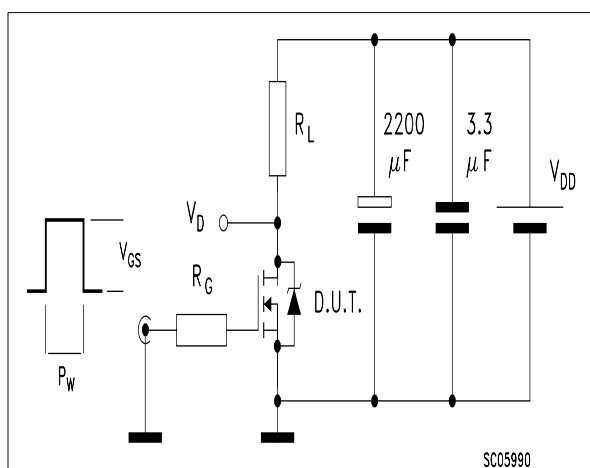
**Fig. 1: Unclamped Inductive Load Test Circuit**



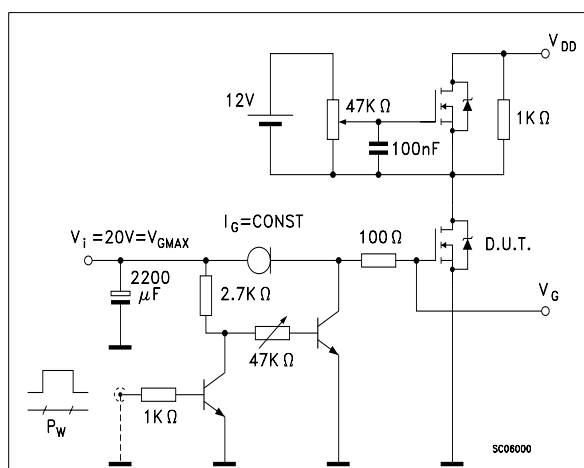
**Fig. 2: Unclamped Inductive Waveform**



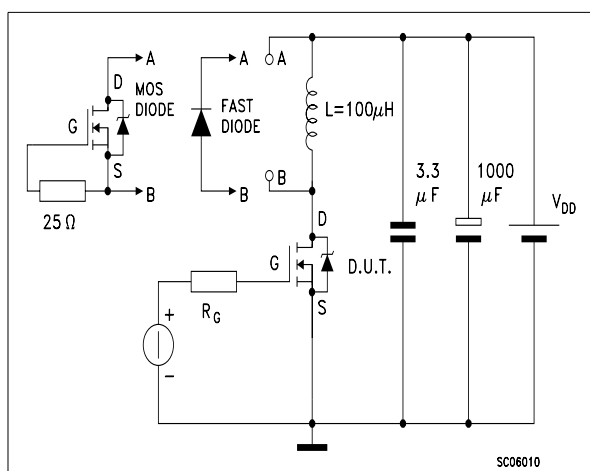
**Fig. 3: Switching Times Test Circuit For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

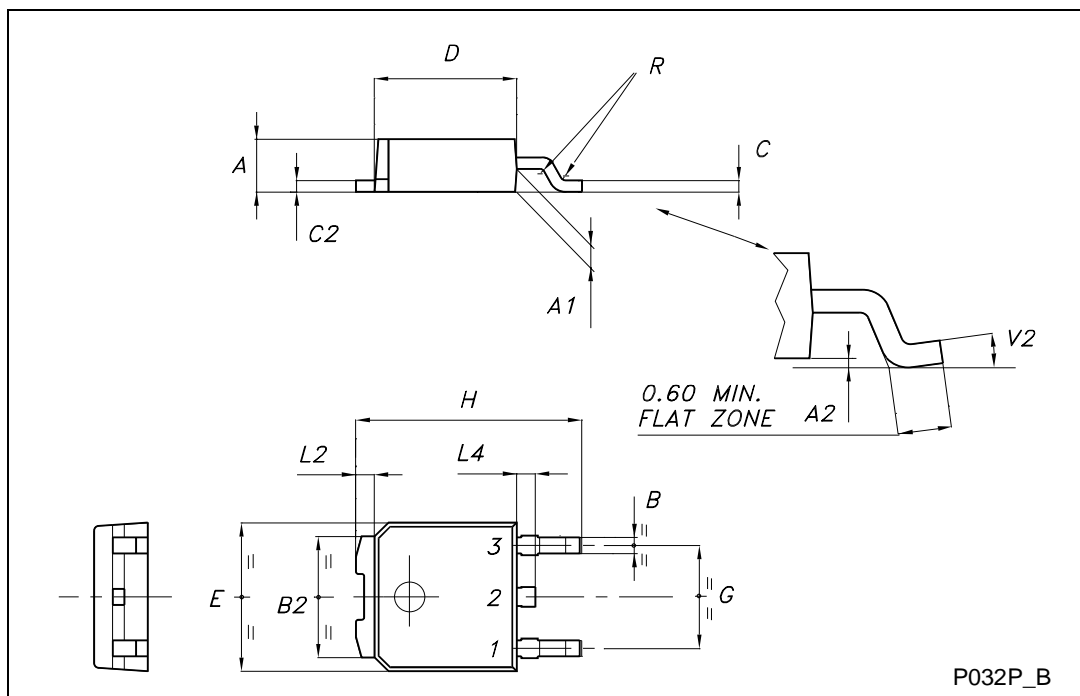


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**

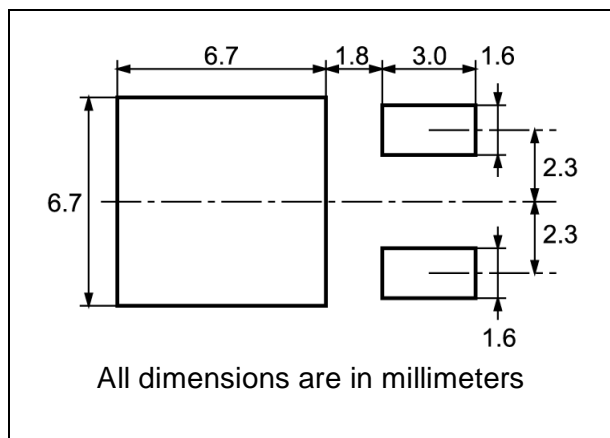


**TO-252 (DPAK) MECHANICAL DATA**

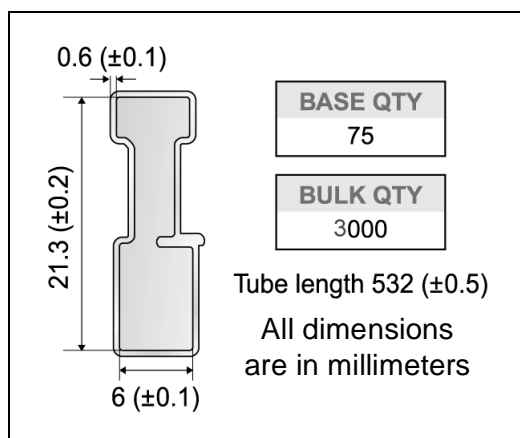
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



**DPAK FOOTPRINT**



**TUBE SHIPMENT (no suffix)\***



**TAPE AND REEL SHIPMENT (suffix "T4")\***

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
1000	1000

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

TOP COVER TAPE

User Direction of Feed

FEED DIRECTION

R min.

Center line of cavity

Bending radius

10 pitches cumulative tolerance on tape +/- 0.2 mm

For machine ref. only including draft and radii concentric around B0

\* on sales type

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